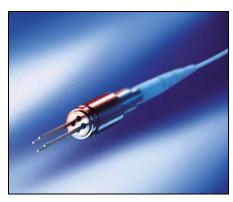


## **Ternary PIN Photodiode**

### SRD00214x SRD00215x

#### **Features**

- InGaAs/InP PIN photodiode
- Designed for applications in fiber-optics communication systems
- Sensitive receiver for 2nd and 3rd optical window (1300 nm and 1550 nm)
- Suitable for bit rates up to 2.5 Gbit/s
- For singlemode and multimode applications SONET OC-1...OC-48, SDH STM-1...STM-16
- Low junction and low package capacitance
- · Fast switching times
- · Low dark current
- Excellent noise immunity
- High reverse current stability from planar structure
- Hermetically sealed TO46 package







# **Pin Configuration**

# **Pin Configuration**

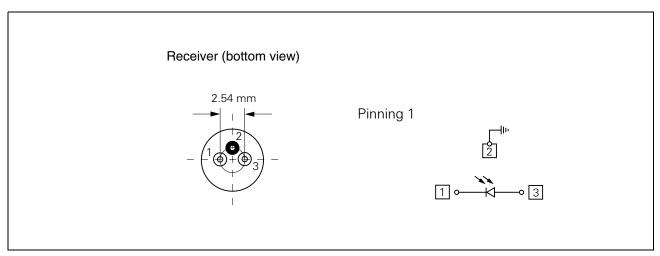


Figure 1 Receiver



**Description** 

#### **Description**

The Infineon optical receiver module has been designed for use in optical networks and is suitable for bit rates up to max. 2.5 Gbit/s if used without any TIA.

The optical receiver module uses a high-speed PIN photodetector optional coupled with a hybrid low noise transimpedance amplifier (PIN-TIA). The optical receiver photodiode can be used for 1310 nm or 1550 nm optical communications.

The PIN photodiode is made of InGaAs/InP and has an active diameter of 75  $\mu$ m. The function of the PIN and PIN-TIA optical receiver module is to detect input optical power, to transduce the incident radiation into current (PIN) and then to convert the current into a voltage (PIN-TIA).

The low input noise current density of the used transimpedance amplifiers in PIN-TIA's provides the optical receiver module, when used with appropriate filtering, with ample sensitivity for realizing minimum input power requirements. Designers of optical receivers can use the module in any application that benefits from integration of the photodiode and TIA into a TO coaxial package. Typical for such applications are receivers for digital crossconnects, digital loop carriers, add/drop-multiplexers and optical network units.

Last but not least the fast switching times, low dark currents and the packaging in a compact and hermetically sealed TO46 make the optical receivers usable in many other fiber optic receiver applications. One application is the use in a Compact realization of a transceiver in one module like the so called BIDI® (Figure 2).

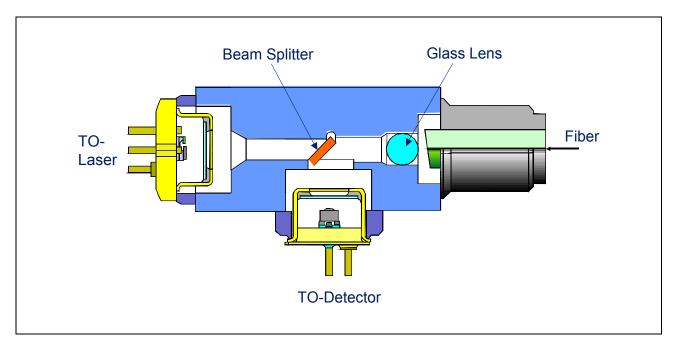


Figure 2 Compact Realization of the Transceiver in One Module



#### **Technical Data**

#### **Technical Data**

All data refer to the full operating temperature range unless otherwise specified.

## **Absolute Maximum Ratings**

Parameter	Symbol	Limit Values		Unit	
		min.	max.		
Module	•	•	<b>.</b>	<b>.</b>	
Operating temperature range at case	$T_{C}$	-40	85	°C	
Storage temperature range	$T_{stg}$	-40	85		
Soldering temperature ( $t_{max} = 10 \text{ s}$ , 2 mm distance from bottom edge of case)	$T_{\mathbb{S}}$		260		
Receiver Diode					
Reverse Voltage	$V_{R}$		20	V	
Forward Current	$I_{F}$		10	mA	
Optical power into the optical port	$P_{port}$		1	mW	

# **Receiver Diode Electro-Optical Characteristics**

Parameter	Symbol	Limit Values			Unit
		min.	typ.	max.	
Spectral sensitivity $V_{\rm R}$ = -2 V, $P_{\rm opt}$ = 1 $\mu W$	$S_{\rm 1310nm} \atop S_{\rm 1550nm}$	0.8	0.9		A/W
Change in Spectral Sensitivity in Operating Temperature Range	$\Delta S$			0.2	%/K
Dark current $V_{\rm R}$ = 2 V, $P_{\rm opt}$ = 0 mW	<i>I</i> <sub>D 25°C</sub> <i>I</i> <sub>D 85°C</sub>			5 50	nA
Total Capacitance $V_{\rm R}$ = 3 V, $f$ = 1 MHz, $V_{\rm RF}$ = 30 mV	С		0.8	1	pF
Rise and fall time (10%90%) $V_{\rm R}$ = 5 V, $P_{\rm opt}$ = (0.11) mW, 50 $\Omega$	$t_{r},t_{f}$		200	300	ps
Cut Off Frequency $\lambda$ = 1310 nm, $V_{\rm R}$ = 5 V, 50 $\Omega$	$f_{\rm 3dB}$	1			GHz
Return Loss, $\lambda = 1310 \text{ nm}$	RL			-27	dB

### **End of Life Time Characteristics**

Parameter	Symbol	Limit Values		Unit
		min.	max.	
Detector Dark Current, $V_R = 2 \text{ V}$ , $T = T_{\text{max}}$	$I_{R}$		400	nA



**Fiber Data** 

## **Fiber Data**

The mechanical fiber characteristics are described in the following table.

### **Fiber Characteristics**

Parameter	Limit Values			Unit
	min.	typ.	max.	
Mode Field Diameter		50		μm
Cladding Diameter	123	125	127	
Mode Field/Cladding Concentricity Error			1	
Cladding Non-circularity			2	%
Mode Field Non-circularity			6	
Cut off Wavelength	1270			nm
Jacket Diameter	0.8		1	mm
Bending Radius	30			
Tensile Strength Fiber Case	5			N
Length	0.8		1.2	m



## **Package Outlines**

# **Package Outlines**

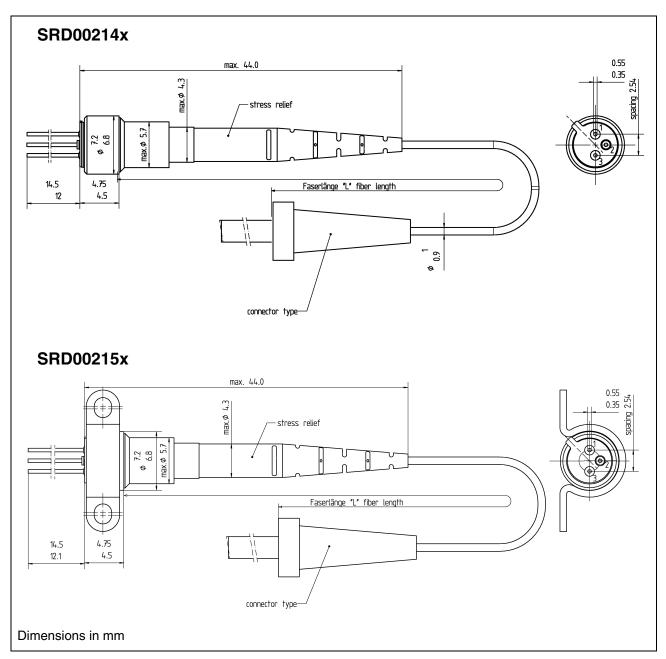


Figure 3



# **Package Outlines**

# **Flange Options**

Туре	Flange
SRD00214x	without
SRD00215x	with

# **Connector Options**

Model	Туре
SRD00214H SRD00215H	MM FC/PC
SRD00214G SRD00215G	SM FC/PC
SRD00214O SRD00215O	MM SC/PC 0°
SRD00214N SRD00215N	SM SC/PC 0°
SRD00214Q SRD00215Q	MM SC 8° APC
SRD00214P SRD00215P	SM SC 8° APC
SRD00214W SRD00215W	MM without connector
SRD00214Z SRD00215Z	SM without connector

Other connectors on request

SRD00214x SRD00215x

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Previous Version:

Page	Subjects (major changes since last revision)		
	Document's layout has been changed: 2002-Aug.		

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